

## SOLUTIONS OFFERED BY SILTRONIC

Silicon wafer	Key Parameter	Device / Application examples
<b>125, 150 mm</b>		
CZ boron doped	misfit reduced	MOSFET, IGBT
CZ phosphorus doped	$\rho < 1 \text{ m}\Omega\text{cm}$	MOSFET
CZ arsenic doped	$\rho < 3 \text{ m}\Omega\text{cm}$	MOSFET, Diode
CZ antimony doped	$\rho < 18 \text{ m}\Omega\text{cm}$	High voltage MOSFET
CZ and epi	thin and thick epi $> 50 \mu\text{m}$	MOSFET, IGBT, PowerIC, Diode
FZ	$\rho \pm 12 \%$	IGBT, MOSFET, Thyristor
HiREF <sup>®</sup> , for all crystal types	diameter, thickness range and $1 \mu\text{m}$ litho capability	Diode, Thyristor
all	thin wafer $< 375 \mu\text{m}$	various
all	multilayer epi	various
all	DSP	various
all	ultraflat wafers for $0.25 \mu\text{m}$ line width	various
<b>200 mm</b>		
CZ boron doped	$\rho \leq 3 \text{ m}\Omega\text{cm}$ , w misfit reduced	IGBT, MOSFET
CZ phosphorus doped	$\rho \leq 1.3 \text{ m}\Omega\text{cm}$	MOSFET
CZ arsenic doped	$\rho < 3 \text{ m}\Omega\text{cm}$	MOSFET, Diode
CZ antimony doped	$\rho < 20 \text{ m}\Omega\text{cm}$	High voltage MOSFET
CZ and epi	think and thick epi $> 50 \mu\text{m}$	MOSFET, IGBT, PowerIC, Diode
FZ	$\rho \pm 12 \%$	IGBT, Diode, Thyristor
all	asymmetric edge profiles	various
all	thin wafers, $525 \mu\text{m}$	various
all	multilayer epi	various